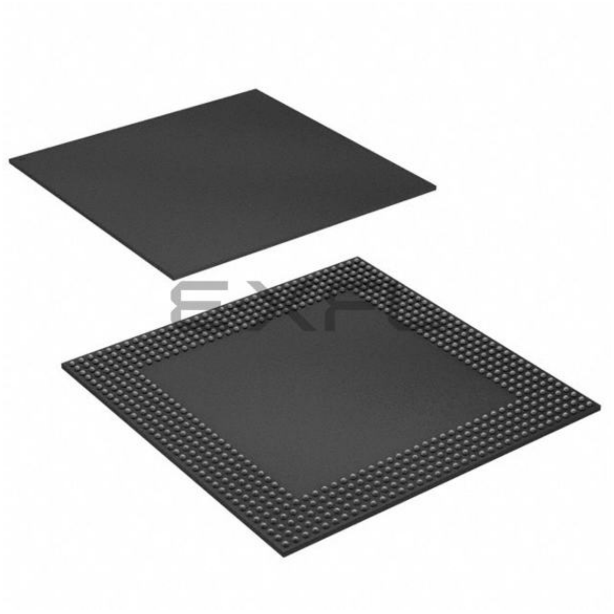
Intel - EPF10K130EBC600-1E Datasheet



Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	6656
Total RAM Bits	65536
Number of I/O	424
Number of Gates	342000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	600-BGA
Supplier Device Package	600-BGA (45x45)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k130ebc600-1e

Email: info@E-XFL.COM Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Similar to the FLEX 10KE architecture, embedded gate arrays are the fastest-growing segment of the gate array market. As with standard gate arrays, embedded gate arrays implement general logic in a conventional “sea-of-gates” architecture. Additionally, embedded gate arrays have dedicated die areas for implementing large, specialized functions. By embedding functions in silicon, embedded gate arrays reduce die area and increase speed when compared to standard gate arrays. While embedded megafunctions typically cannot be customized, FLEX 10KE devices are programmable, providing the designer with full control over embedded megafunctions and general logic, while facilitating iterative design changes during debugging.

Each FLEX 10KE device contains an embedded array and a logic array. The embedded array is used to implement a variety of memory functions or complex logic functions, such as digital signal processing (DSP), wide data-path manipulation, microcontroller applications, and data-transformation functions. The logic array performs the same function as the sea-of-gates in the gate array and is used to implement general logic such as counters, adders, state machines, and multiplexers. The combination of embedded and logic arrays provides the high performance and high density of embedded gate arrays, enabling designers to implement an entire system on a single device.

FLEX 10KE devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers the EPC1, EPC2, and EPC16 configuration devices, which configure FLEX 10KE devices via a serial data stream. Configuration data can also be downloaded from system RAM or via the Altera BitBlaster™, ByteBlasterMV™, or MasterBlaster download cables. After a FLEX 10KE device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Because reconfiguration requires less than 85 ms, real-time changes can be made during system operation.

FLEX 10KE devices contain an interface that permits microprocessors to configure FLEX 10KE devices serially or in-parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat a FLEX 10KE device as memory and configure it by writing to a virtual memory location, making it easy to reconfigure the device.

For more information on FLEX device configuration, see the following documents:

- *Configuration Devices for APEX & FLEX Devices Data Sheet*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *MasterBlaster Download Cable Data Sheet*
- *Application Note 116 (Configuring APEX 20K, FLEX 10K, & FLEX 6000 Devices)*

FLEX 10KE devices are supported by the Altera development systems, which are integrated packages that offer schematic, text (including AHDL), and waveform design entry, compilation and logic synthesis, full simulation and worst-case timing analysis, and device configuration. The Altera software provides EDIF 2 0 0 and 3 0 0, LPM, VHDL, Verilog HDL, and other interfaces for additional design entry and simulation support from other industry-standard PC- and UNIX workstation-based EDA tools.

The Altera software works easily with common gate array EDA tools for synthesis and simulation. For example, the Altera software can generate Verilog HDL files for simulation with tools such as Cadence Verilog-XL. Additionally, the Altera software contains EDA libraries that use device-specific features such as carry chains, which are used for fast counter and arithmetic functions. For instance, the Synopsys Design Compiler library supplied with the Altera development system includes DesignWare functions that are optimized for the FLEX 10KE architecture.

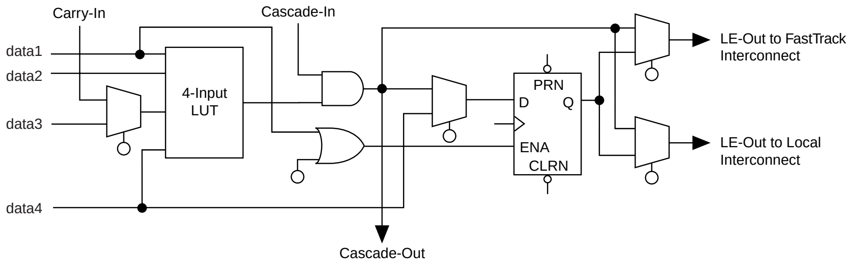
The Altera development system runs on Windows-based PCs and Sun SPARCstation, and HP 9000 Series 700/800.

See the *MAX+PLUS II Programmable Logic Development System & Software Data Sheet* and the *Quartus Programmable Logic Development System & Software Data Sheet* for more information.

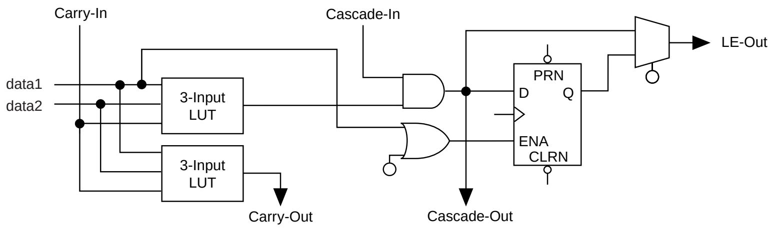
Figure 11 shows the LE operating modes.

Figure 11. FLEX 10KE LE Operating Modes

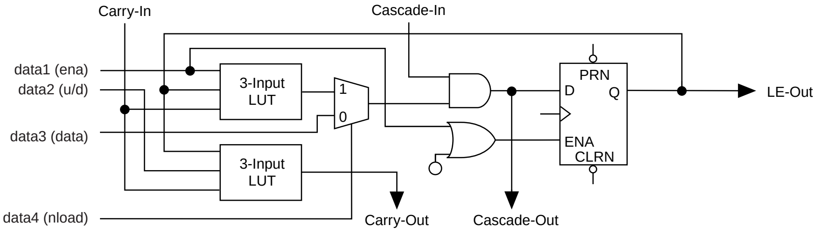
Normal Mode



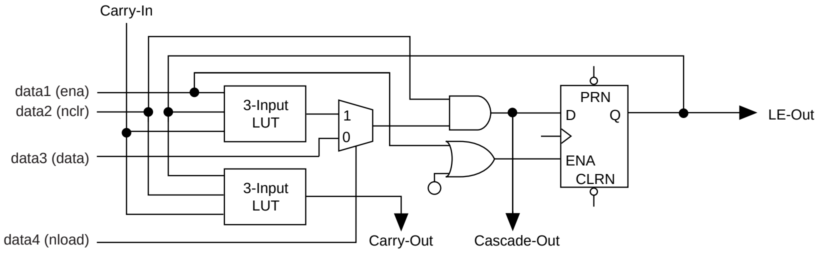
Arithmetic Mode



Up/Down Counter Mode



Clearable Counter Mode



For improved routing, the row interconnect consists of a combination of full-length and half-length channels. The full-length channels connect to all LABs in a row; the half-length channels connect to the LABs in half of the row. The EAB can be driven by the half-length channels in the left half of the row and by the full-length channels. The EAB drives out to the full-length channels. In addition to providing a predictable, row-wide interconnect, this architecture provides increased routing resources. Two neighboring LABs can be connected using a half-row channel, thereby saving the other half of the channel for the other half of the row.

Table 7 summarizes the FastTrack Interconnect routing structure resources available in each FLEX 10KE device.

Table 7. FLEX 10KE FastTrack Interconnect Resources

Device	Rows	Channels per Row	Columns	Channels per Column
EPF10K30E	6	216	36	24
EPF10K50E EPF10K50S	10	216	36	24
EPF10K100E	12	312	52	24
EPF10K130E	16	312	52	32
EPF10K200E EPF10K200S	24	312	52	48

In addition to general-purpose I/O pins, FLEX 10KE devices have six dedicated input pins that provide low-skew signal distribution across the device. These six inputs can be used for global clock, clear, preset, and peripheral output enable and clock enable control signals. These signals are available as control signals for all LABs and IOEs in the device. The dedicated inputs can also be used as general-purpose data inputs because they can feed the local interconnect of each LAB in the device.

Figure 14 shows the interconnection of adjacent LABs and EABs, with row, column, and local interconnects, as well as the associated cascade and carry chains. Each LAB is labeled according to its location: a letter represents the row and a number represents the column. For example, LAB B3 is in row B, column 3.

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels is different for each IOE (see Figure 17).

Figure 17. FLEX 10KE Column-to-IOE Connections

The values for m and n are provided in Table 11.

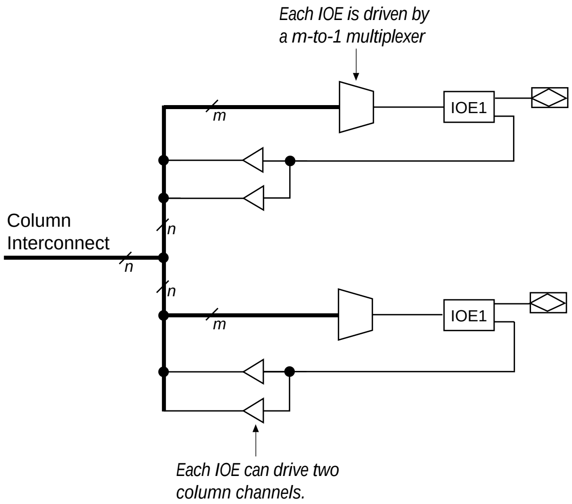


Table 11 lists the FLEX 10KE column-to-IOE interconnect resources.

Table 11. FLEX 10KE Column-to-IOE Interconnect Resources

Device	Channels per Column *(n)*	Column Channels per Pin *(m)*
EPF10K30E	24	16
EPF10K50E EPF10K50S	24	16
EPF10K100E	24	16
EPF10K130E	32	24
EPF10K200E EPF10K200S	48	40

PCI Pull-Up Clamping Diode Option

FLEX 10KE devices have a pull-up clamping diode on every I/O, dedicated input, and dedicated clock pin. PCI clamping diodes clamp the signal to the V_{CCIO} value and are required for 3.3-V PCI compliance. Clamping diodes can also be used to limit overshoot in other systems.

Clamping diodes are controlled on a pin-by-pin basis. When V_{CCIO} is 3.3 V, a pin that has the clamping diode option turned on can be driven by a 2.5-V or 3.3-V signal, but not a 5.0-V signal. When V_{CCIO} is 2.5 V, a pin that has the clamping diode option turned on can be driven by a 2.5-V signal, but not a 3.3-V or 5.0-V signal. Additionally, a clamping diode can be activated for a subset of pins, which would allow a device to bridge between a 3.3-V PCI bus and a 5.0-V device.

Slew-Rate Control

The output buffer in each IOE has an adjustable output slew rate that can be configured for low-noise or high-speed performance. A slower slew rate reduces system noise and adds a maximum delay of 4.3 ns. The fast slew rate should be used for speed-critical outputs in systems that are adequately protected against noise. Designers can specify the slew rate pin-by-pin or assign a default slew rate to all pins on a device-wide basis. The slow slew rate setting affects the falling edge of the output.

Open-Drain Output Option

FLEX 10KE devices provide an optional open-drain output (electrically equivalent to open-collector output) for each I/O pin. This open-drain output enables the device to provide system-level control signals (e.g., interrupt and write enable signals) that can be asserted by any of several devices. It can also provide an additional wired-`OR` plane.

MultiVolt I/O Interface

The FLEX 10KE device architecture supports the MultiVolt I/O interface feature, which allows FLEX 10KE devices in all packages to interface with systems of differing supply voltages. These devices have one set of V_{CC} pins for internal operation and input buffers (`VCCINT`), and another set for I/O output drivers (`VCCIO`).

The `VCCINT` pins must always be connected to a 2.5-V power supply. With a 2.5-V V_{CCINT} level, input voltages are compatible with 2.5-V, 3.3-V, and 5.0-V inputs. The `VCCIO` pins can be connected to either a 2.5-V or 3.3-V power supply, depending on the output requirements. When the `VCCIO` pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When the `VCCIO` pins are connected to a 3.3-V power supply, the output high is at 3.3 V and is therefore compatible with 3.3-V or 5.0-V systems. Devices operating with V_{CCIO} levels higher than 3.0 V achieve a faster timing delay of t_{OD2} instead of t_{OD1}.

Table 14 summarizes FLEX 10KE MultiVolt I/O support.

Table 14. FLEX 10KE MultiVolt I/O Support

V_{CCIO} (V)	Input Signal (V)			Output Signal (V)		
	2.5	3.3	5.0	2.5	3.3	5.0
2.5	✓	✓ (1)	✓ (1)	✓		
3.3	✓	✓	✓ (1)	✓ (2)	✓	✓

Notes:

(1) The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}.

(2) When V_{CCIO} = 3.3 V, a FLEX 10KE device can drive a 2.5-V device that has 3.3-V tolerant inputs.

Open-drain output pins on FLEX 10KE devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the open-drain pin is active, it will drive low. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

Power Sequencing & Hot-Socketing

Because FLEX 10KE devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The V_{CCIO} and V_{CCINT} power planes can be powered in any order.

Signals can be driven into FLEX 10KE devices before and during power up without damaging the device. Additionally, FLEX 10KE devices do not drive out during power up. Once operating conditions are reached, FLEX 10KE devices operate as specified by the user.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10KE devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. FLEX 10KE devices can also be configured using the JTAG pins through the BitBlaster or ByteBlasterMV download cable, or via hardware that uses the Jam™ STAPL programming and test language. JTAG boundary-scan testing can be performed before or after configuration, but not during configuration. FLEX 10KE devices support the JTAG instructions shown in Table 15.

Table 15. FLEX 10KE JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern to be output at the device pins.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the `TDI` and `TDO` pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the `TDI` and `TDO` pins, allowing the USERCODE to be serially shifted out of `TDO`.
IDCODE	Selects the IDCODE register and places it between `TDI` and `TDO`, allowing the IDCODE to be serially shifted out of `TDO`.
ICR Instructions	These instructions are used when configuring a FLEX 10KE device via JTAG ports with a BitBlaster or ByteBlasterMV download cable, or using a Jam File (**.jam**) or Jam Byte-Code File (**.jbc**) via an embedded processor.

The instruction register length of FLEX 10KE devices is 10 bits. The USERCODE register length in FLEX 10KE devices is 32 bits; 7 bits are determined by the user, and 25 bits are pre-determined. Tables 16 and 17 show the boundary-scan register length and device IDCODE information for FLEX 10KE devices.

Table 16. FLEX 10KE Boundary-Scan Register Length

Device	Boundary-Scan Register Length
EPF10K30E	690
EPF10K50E EPF10K50S	798
EPF10K100E	1,050
EPF10K130E	1,308
EPF10K200E EPF10K200S	1,446

Table 22. FLEX 10KE 2.5-V Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7, 0.5 × V_{CCIO} *(8)*		5.75	V
V_{IL}	Low-level input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(8)*	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –8 mA DC, V_{CCIO} = 3.00 V *(9)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(9)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(9)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(9)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(9)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(9)*	1.7			V
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(10)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(10)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(10)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(10)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(10)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(10)*			0.7	V
I_I	Input pin leakage current	V_I = $V_{CCIOmax}$ to 0 V *(11)*	–10		10	μA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = $V_{CCIOmax}$ to 0 V *(11)*	–10		10	μA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load, no toggling inputs		5		mA
		V_I = ground, no load, no toggling inputs *(12)*		10		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(13)*	20		50	k¾
		V_{CCIO} = 2.3 V *(13)*	30		80	k¾

Table 26. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABRE1}	Read enable delay to EAB for combinatorial input	
t_{EABRE2}	Read enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABBYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{EABCLR}	EAB register asynchronous clear time to output delay	
t_{AA}	Address access delay (including the read enable to output delay)	
t_{WP}	Write pulse width	
t_{RP}	Read pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	*(5)*
t_{WDH}	Data hold time after falling edge of write pulse	*(5)*
t_{WASU}	Address setup time before rising edge of write pulse	*(5)*
t_{WAH}	Address hold time after falling edge of write pulse	*(5)*
t_{RASU}	Address setup time with respect to the falling edge of the read enable	
t_{RAH}	Address hold time with respect to the falling edge of the read enable	
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

Table 30. External Bidirectional Timing Parameters *Note (9)*

Symbol	Parameter	Conditions
$t_{INSUBIDIR}$	Setup time for bi-directional pins with global clock at same-row or same-column LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at same-row or same-column LE register	
t_{INH}	Hold time with global clock at IOE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 35 pF
$t_{XZBIDIR}$	Synchronous IOE output buffer disable delay	C1 = 35 pF
$t_{ZXBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate= off	C1 = 35 pF

Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.
(2) Operating conditions: VCCIO = 3.3 V ±10% for commercial or industrial use.
(3) Operating conditions: VCCIO = 2.5 V ±5% for commercial or industrial use in EPF10K30E, EPF10K50S, EPF10K100E, EPF10K130E, and EPF10K200S devices.
(4) Operating conditions: VCCIO = 3.3 V.
(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the `WE` signal is registered.
(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.
(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.
(8) Contact Altera Applications for test circuit specifications and test conditions.
(9) This timing parameter is sample-tested only.
(10) This parameter is measured with the measurement and test conditions, including load, specified in the PCI Local Bus Specification, revision 2.2.

Table 31. EPF10K30E Device LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CGENR}		0.1		0.1		0.2	ns
t_{CASC}		0.6		0.8		1.0	ns
t_C		0.0		0.0		0.0	ns
t_{CO}		0.3		0.4		0.5	ns
t_{COMB}		0.4		0.4		0.6	ns
t_{SU}	0.4		0.6		0.6		ns
t_H	0.7		1.0		1.3		ns
t_{PRE}		0.8		0.9		1.2	ns
t_{CLR}		0.8		0.9		1.2	ns
t_{CH}	2.0		2.5		2.5		ns
t_{CL}	2.0		2.5		2.5		ns

Table 32. EPF10K30E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		2.4		2.8		3.8	ns
t_{IOC}		0.3		0.4		0.5	ns
t_{IOCO}		1.0		1.1		1.6	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	1.2		1.4		1.9		ns
t_{IOH}	0.3		0.4		0.5		ns
t_{IOCLR}		1.0		1.1		1.6	ns
t_{OD1}		1.9		2.3		3.0	ns
t_{OD2}		1.4		1.8		2.5	ns
t_{OD3}		4.4		5.2		7.0	ns
t_{XZ}		2.7		3.1		4.3	ns
t_{ZX1}		2.7		3.1		4.3	ns
t_{ZX2}		2.2		2.6		3.8	ns
t_{ZX3}		5.2		6.0		8.3	ns
t_{INREG}		3.4		4.1		5.5	ns
t_{IOFD}		0.8		1.3		2.4	ns
t_{INCOMB}		0.8		1.3		2.4	ns

Table 33. EPF10K30E Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.7		2.0		2.3	ns
$t_{EABDATA1}$		0.6		0.7		0.8	ns
t_{EABWE1}		1.1		1.3		1.4	ns
t_{EABWE2}		0.4		0.4		0.5	ns
t_{EABRE1}		0.8		0.9		1.0	ns
t_{EABRE2}		0.4		0.4		0.5	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.3		0.4	ns
$t_{EABBYPASS}$		0.5		0.6		0.7	ns
t_{EABSU}	0.9		1.0		1.2		ns
t_{EABH}	0.4		0.4		0.5		ns
t_{EABCLR}	0.3		0.3		0.3		ns
t_{AA}		3.2		3.8		4.4	ns
t_{WP}	2.5		2.9		3.3		ns
t_{RP}	0.9		1.1		1.2		ns
t_{WDSU}	0.9		1.0		1.1		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.7		2.0		2.3		ns
t_{WAH}	1.8		2.1		2.4		ns
t_{RASU}	3.1		3.7		4.2		ns
t_{RAH}	0.2		0.2		0.2		ns
t_{WO}		2.5		2.9		3.3	ns
t_{DD}		2.5		2.9		3.3	ns
t_{EABOUT}		0.5		0.6		0.7	ns
t_{EABCH}	1.5		2.0		2.3		ns
t_{EABCL}	2.5		2.9		3.3		ns

Table 37. EPF10K30E External Bidirectional Timing Parameters Notes (1), (2)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (3)	2.8		3.9		5.2		ns
$t_{INHBIDIR}$ (3)	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ (4)	3.8		4.9		–		ns
$t_{INHBIDIR}$ (4)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (3)	2.0	4.9	2.0	5.9	2.0	7.6	ns
$t_{XZBIDIR}$ (3)		6.1		7.5		9.7	ns
$t_{ZXBIDIR}$ (3)		6.1		7.5		9.7	ns
$t_{OUTCOBIDIR}$ (4)	0.5	3.9	0.5	4.9	–	–	ns
$t_{XZBIDIR}$ (4)		5.1		6.5		–	ns
$t_{ZXBIDIR}$ (4)		5.1		6.5		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 38 through 44 show EPF10K50E device internal and external timing parameters.

Table 38. EPF10K50E Device LE Timing Microparameters (Part 1 of 2) Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.6		0.9		1.3	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.7		0.8		1.1	ns
t_{PACKED}		0.4		0.5		0.6	ns
t_{EN}		0.6		0.7		0.9	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.5		0.5		0.8	ns
t_{CGENR}		0.2		0.2		0.3	ns
t_{CASC}		0.8		1.0		1.4	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.7		0.7		0.9	ns
t_{COMB}		0.5		0.6		0.8	ns
t_{SU}	0.7		0.7		0.8		ns

Table 54. EPF10K130E Device EAB Internal Microparameters (Part 2 of 2) Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DD}		1.5		2.0		2.6	ns
t_{EABOUT}		0.2		0.3		0.3	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	2.7		3.5		4.7		ns

Table 55. EPF10K130E Device EAB Internal Timing Macroparameters Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		5.9		7.5		9.9	ns
$t_{EABRCOMB}$	5.9		7.5		9.9		ns
$t_{EABRCREG}$	5.1		6.4		8.5		ns
t_{EABWP}	2.7		3.5		4.7		ns
$t_{EABWCOMB}$	5.9		7.7		10.3		ns
$t_{EABWCREG}$	5.4		7.0		9.4		ns
t_{EABDD}		3.4		4.5		5.9	ns
$t_{EABDATACO}$		0.5		0.7		0.8	ns
$t_{EABDATASU}$	0.8		1.0		1.4		ns
$t_{EABDATAH}$	0.1		0.1		0.2		ns
$t_{EABWESU}$	1.1		1.4		1.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.0		1.3		1.7		ns
t_{EABWDH}	0.2		0.2		0.3		ns
$t_{EABWASU}$	4.1		5.1		6.8		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		3.4		4.5		5.9	ns

Table 56. EPF10K130E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		2.8		3.5		4.4	ns
t_{DIN2LE}		0.7		1.2		1.6	ns
$t_{DIN2DATA}$		1.6		1.9		2.2	ns
$t_{DCLK2IOE}$		1.6		2.1		2.7	ns
$t_{DCLK2LE}$		0.7		1.2		1.6	ns
$t_{SAMELAB}$		0.1		0.2		0.2	ns
$t_{SAMEROW}$		1.9		3.4		5.1	ns
$t_{SAMECOLUMN}$		0.9		2.6		4.4	ns
$t_{DIFFROW}$		2.8		6.0		9.5	ns
$t_{TWOROWS}$		4.7		9.4		14.6	ns
$t_{LEPERIPH}$		3.1		4.7		6.9	ns
$t_{LABCARRY}$		0.6		0.8		1.0	ns
$t_{LABCASC}$		0.9		1.2		1.6	ns

Table 57. EPF10K130E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(3)*	1.9		2.1		3.0		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.0	2.0	7.0	2.0	9.2	ns
t_{INSU} *(4)*	0.9		1.1		–		ns
t_{INH} *(4)*	0.0		0.0		–		ns
t_{OUTCO} *(4)*	0.5	4.0	0.5	6.0	–	–	ns
t_{PCISU}	3.0		6.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	6.9	–	–	ns

Table 59. EPF10K200E Device LE Timing Microparameters *(Part 2 of 2)* *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{H}	0.9		1.1		1.5		ns
t_{PRE}		0.5		0.6		0.8	ns
t_{CLR}		0.5		0.6		0.8	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 60. EPF10K200E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.6		1.9		2.6	ns
t_{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		1.6		1.9		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		0.9		1.2		ns
t_{IOH}	0.7		0.8		1.1		ns
t_{IOCLR}		0.2		0.2		0.3	ns
t_{OD1}		0.6		0.7		0.9	ns
t_{OD2}		0.1		0.2		0.7	ns
t_{OD3}		2.5		3.0		3.9	ns
t_{XZ}		4.4		5.3		7.1	ns
t_{ZX1}		4.4		5.3		7.1	ns
t_{ZX2}		3.9		4.8		6.9	ns
t_{ZX3}		6.3		7.6		10.1	ns
t_{INREG}		4.8		5.7		7.7	ns
t_{IOFD}		1.5		1.8		2.4	ns
t_{INCOMB}		1.5		1.8		2.4	ns

Table 66. EPF10K50S Device LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CGENR}		0.1		0.1		0.1	ns
t_{CASC}		0.5		0.8		1.0	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.6		0.6		0.7	ns
t_{COMB}		0.3		0.4		0.5	ns
t_{SU}	0.5		0.6		0.7		ns
t_{H}	0.5		0.6		0.8		ns
t_{PRE}		0.4		0.5		0.7	ns
t_{CLR}		0.8		1.0		1.2	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

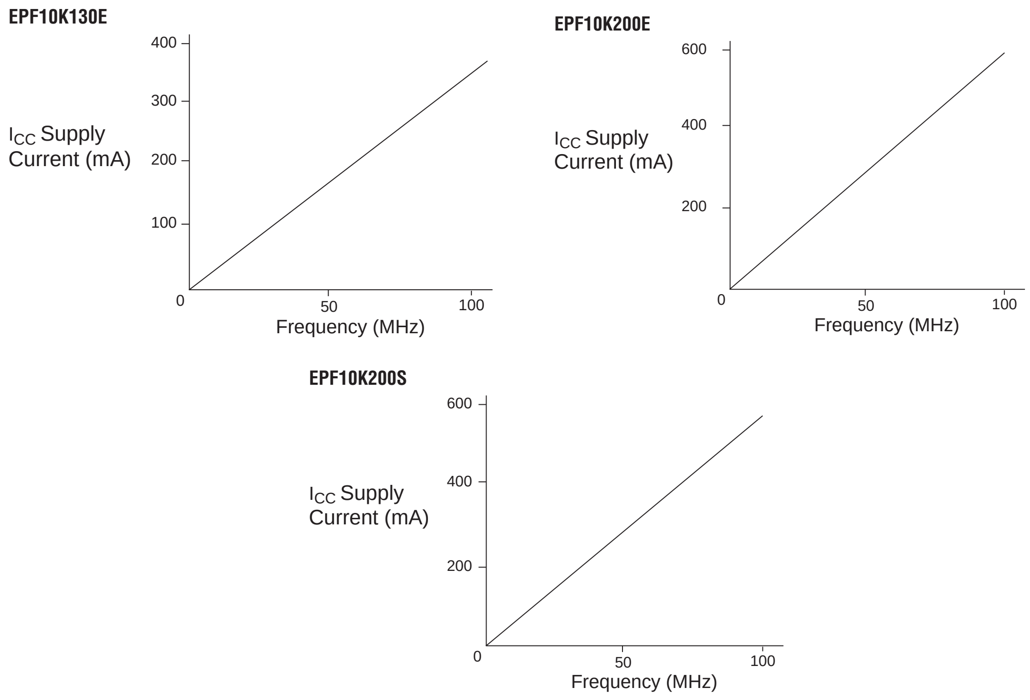
Table 67. EPF10K50S Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.3		1.3		1.9	ns
t_{IOC}		0.3		0.4		0.4	ns
t_{IOCO}		1.7		2.1		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		1.0		1.3		ns
t_{IOH}	0.4		0.5		0.6		ns
t_{IOCLR}		0.2		0.2		0.4	ns
t_{OD1}		1.2		1.2		1.9	ns
t_{OD2}		0.7		0.8		1.7	ns
t_{OD3}		2.7		3.0		4.3	ns
t_{XZ}		4.7		5.7		7.5	ns
t_{ZX1}		4.7		5.7		7.5	ns
t_{ZX2}		4.2		5.3		7.3	ns
t_{ZX3}		6.2		7.5		9.9	ns
t_{INREG}		3.5		4.2		5.6	ns
t_{IOFD}		1.1		1.3		1.8	ns
t_{INCOMB}		1.1		1.3		1.8	ns

Table 68. EPF10K50S Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.7		2.4		3.2	ns
$t_{EABDATA2}$		0.4		0.6		0.8	ns
t_{EABWE1}		1.0		1.4		1.9	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0.0		0.0		0.0	
t_{EABRE2}		0.4		0.6		0.8	
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		1.1		1.5	ns
$t_{EABBYPASS}$		0.0		0.0		0.0	ns
t_{EABSU}	0.7		1.0		1.3		ns
t_{EABH}	0.4		0.6		0.8		ns
t_{EABCLR}	0.8		1.1		1.5		
t_{AA}		2.0		2.8		3.8	ns
t_{WP}	2.0		2.8		3.8		ns
t_{RP}	1.0		1.4		1.9		
t_{WDSU}	0.5		0.7		0.9		ns
t_{WDH}	0.1		0.1		0.2		ns
t_{WASU}	1.0		1.4		1.9		ns
t_{WAH}	1.5		2.1		2.9		ns
t_{RASU}	1.5		2.1		2.8		
t_{RAH}	0.1		0.1		0.2		
t_{WO}		2.1		2.9		4.0	ns
t_{DD}		2.1		2.9		4.0	ns
t_{EABOUT}		0.0		0.0		0.0	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	1.5		2.0		2.5		ns

Figure 31. FLEX 10KE $I_{CCACTIVE}$ vs. Operating Frequency (Part 2 of 2)



Configuration & Operation

The FLEX 10KE architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

Operating Modes

The FLEX 10KE architecture uses SRAM configuration elements that require configuration data to be loaded every time the circuit powers up. The process of physically loading the SRAM data into the device is called *configuration*. Before configuration, as V_{CC} rises, the device initiates a Power-On Reset (POR). This POR event clears the device and prepares it for configuration. The FLEX 10KE POR time does not exceed 50 µs.

When configuring with a configuration device, refer to the respective configuration device data sheet for POR timing information.